

06-06-07

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicants:	KIM, Hyun-Jae and KANG, Myung-Koo		
Assignee:	SAMSUNG ELECTRONICS CO., LTD.		
Title:	METHOD OF POLYCRYSTALLIZATION, METHOD OF MANUFACTURING POLYSILICON THIN FILM TRANSISTOR, AND LASER IRRADIATION DEVICE THEREFOR		
Application No.:	10/532,459	Filing Date:	11/02/2005
Examiner:	BOOTH, Richard A.	Group Art Unit:	2812
Docket No.:	AB-1432 US	Confirmation No.:	1783

San Jose, California
June 4, 2007

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

RESPONSE TO RESTRICTION REQUIREMENT

Dear Sir:

In response to the Office Action having a mailing date of May 4, 20007, Applicants hereby elect Group II (claims 2-7, drawn to a method of making a thin film transistor) for further prosecution. Applicants withdraw the non-elected claim of Group I (claim 1, drawn to a device for irradiating a laser beam), reserving the right to prosecute that claim in another application.

The Examiner is invited to call the undersigned at (408) 392-9250 with any questions regarding the above-identified application.

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Respectfully submitted,

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